ALPHA & OMEGA SEMICONDUCTOR

AON7508

30V N-Channel AlphaMOS

General Description

- Latest Trench Power AlphaMOS (αMOS LV) technology
- Very Low RDS(on) at 4.5V_{GS}
- Low Gate Charge
- High Current Capability
- RoHS and Halogen-Free Compliant

Application

- DC/DC Converters in Computing, Servers, and POL
- Isolated DC/DC Converters in Telecom and Industrial

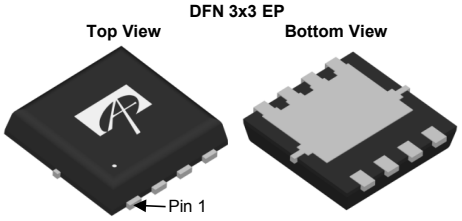
Product Summary

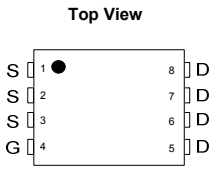
V_{DS}	30V
I_D (at V_{GS}=10V)	32A
$R_{DS(ON)}$ (at V_{GS}=10V)	< 3.0mΩ
$R_{DS(ON)}$ (at V_{GS}=4.5V)	< 4.6mΩ

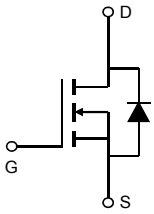
100% UIS Tested
100% R_g Tested

Green Product

DFN 3x3 EP







Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [G]	T_C=25°C	I_D	32	A
	T_C=100°C		25	
Pulsed Drain Current [C]		I_{DM}	128	
Continuous Drain Current	T_A=25°C	I_{DSM}	26	A
	T_A=70°C		21	
Avalanche Current [C]		I_{AS}	50	A
Avalanche energy L=0.05mH [C]		E_{AS}	63	mJ
V_{DS} Spike	100ns	V_{SPIKE}	36	V
Power Dissipation [B]	T_C=25°C	P_D	62.5	W
	T_C=100°C		25	
Power Dissipation [A]	T_A=25°C	P_{DSM}	3.1	W
	T_A=70°C		2	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	30	40	°C/W
Maximum Junction-to-Ambient [A D]	Steady-State		60	75	°C/W
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	1.5	2	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30V, V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±20V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250µA	1.2	1.8	2.2	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=20A		2.4	3	mΩ
		T_J=125°C		3.3	4.1	
		V_{GS}=4.5V, I_D=20A		3.5	4.6	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		85		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.68	1	V
I_S	Maximum Body-Diode Continuous Current [G]				32	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		1835		pF
C_{oss}	Output Capacitance			940		pF
C_{rss}	Reverse Transfer Capacitance			90		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	0.7	1.5	2.3	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=20A		29	40	nC
Q_g(4.5V)	Total Gate Charge			13.6	19	nC
Q_{gs}	Gate Source Charge			5.8		nC
Q_{gd}	Gate Drain Charge			5.3		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=0.75Ω, R_{GEN}=3Ω		7.9		ns
t_r	Turn-On Rise Time			4.0		ns
$t_{D(off)}$	Turn-Off DelayTime			27.3		ns
t_f	Turn-Off Fall Time			6.5		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=20A, dI/dt=500A/µs		19		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=20A, dI/dt=500A/µs		36.7		nC

A. The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A =25° C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150° C. The value in any given application depends on the user's specific board design.

B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Single pulse width limited by junction temperature $T_{J(MAX)}$=150° C.

D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C. The SOA curve provides a single pulse rating.

G. The maximum current rating is package limited.

H. These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25° C.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

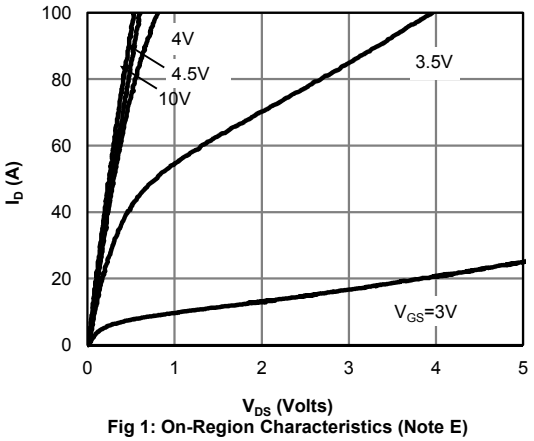


Fig 1: On-Region Characteristics (Note E)

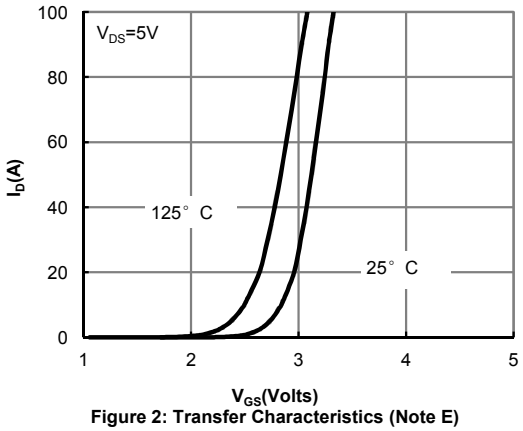


Figure 2: Transfer Characteristics (Note E)

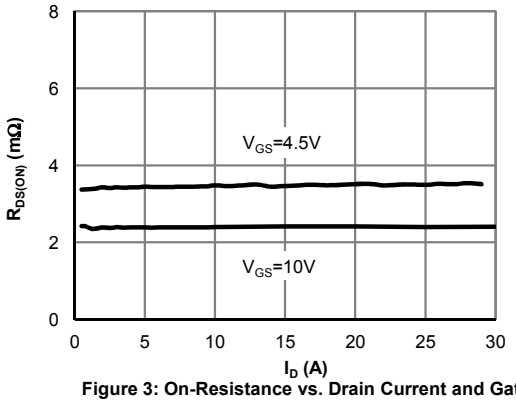


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

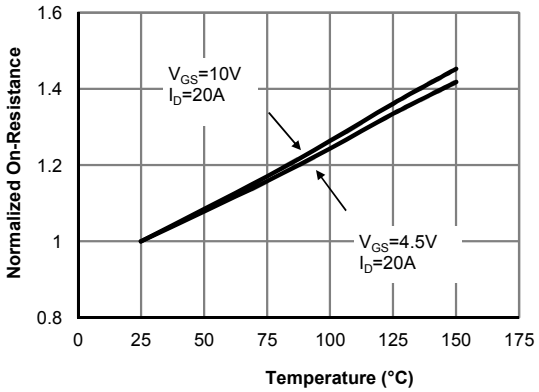


Figure 4: On-Resistance vs. Junction Temperature (Note E)

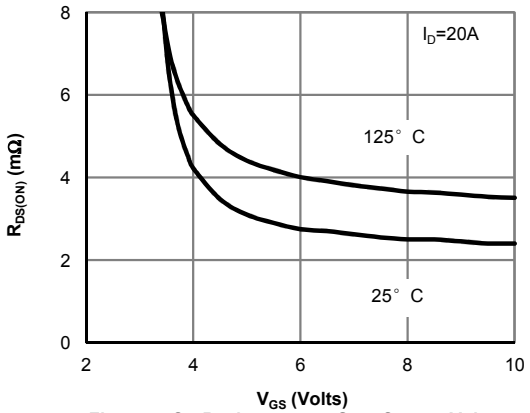


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

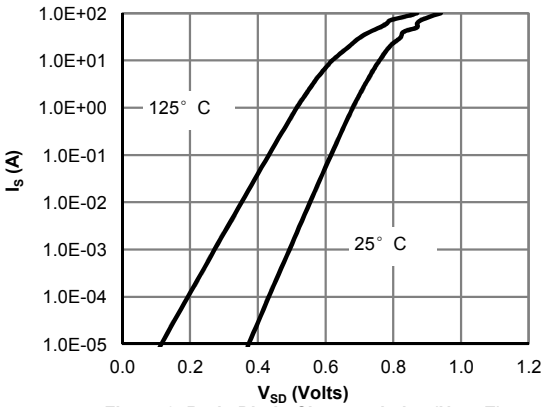


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

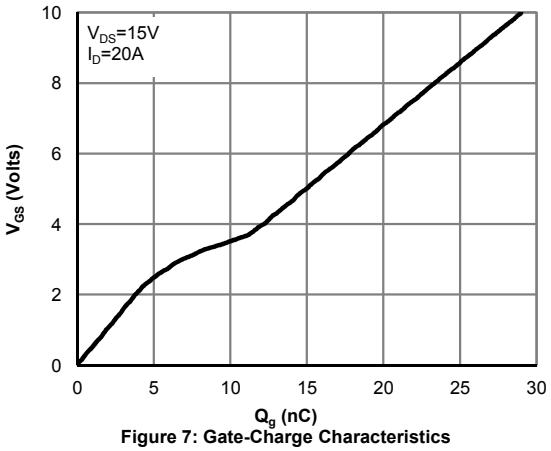


Figure 7: Gate-Charge Characteristics

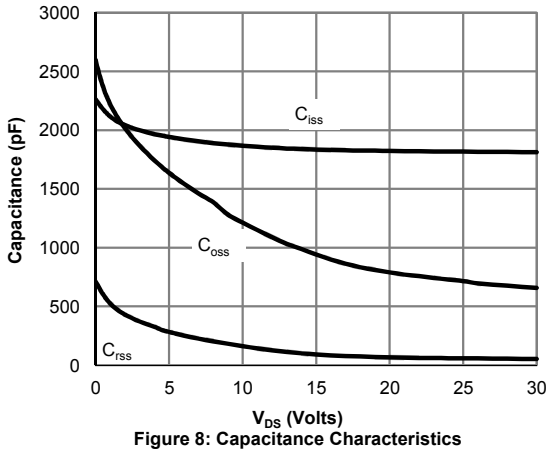


Figure 8: Capacitance Characteristics

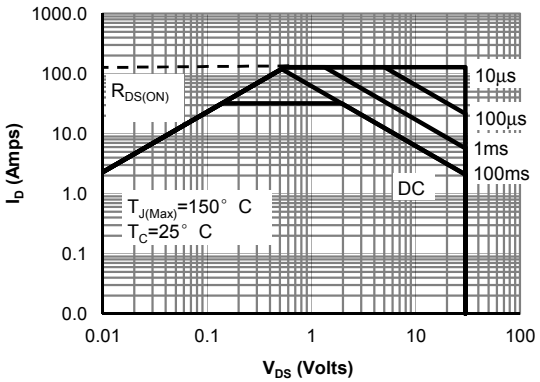


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

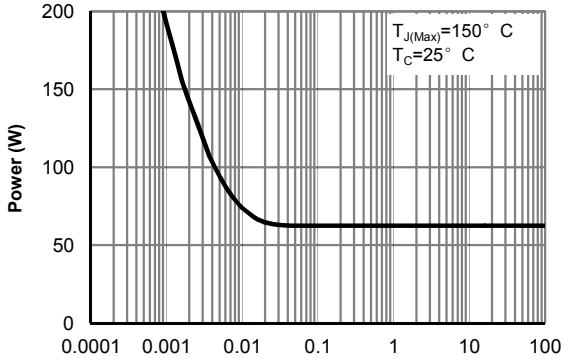


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

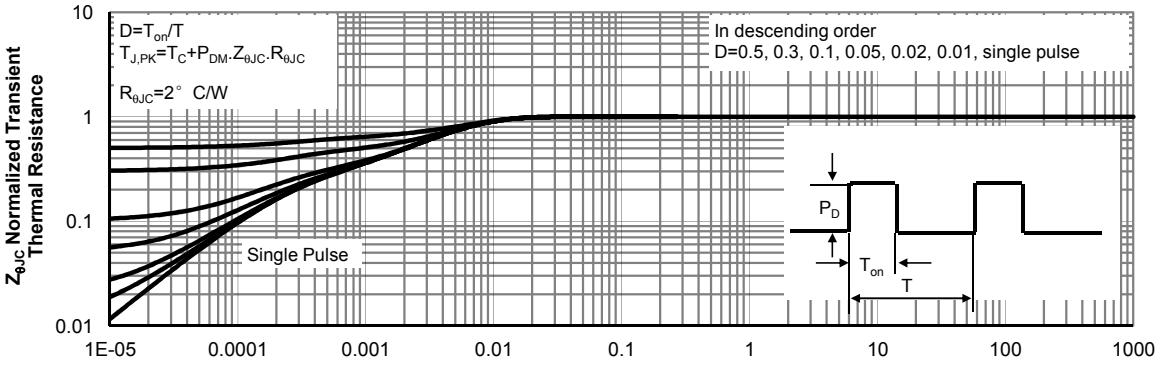


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

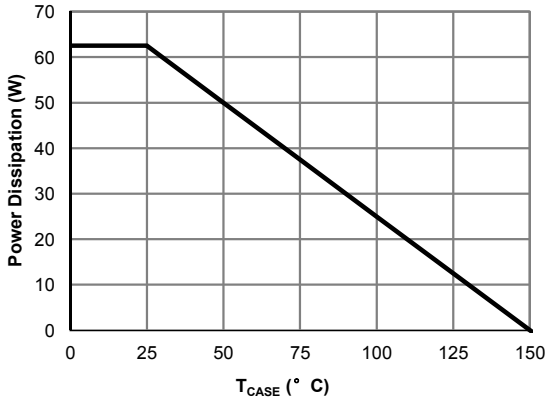


Figure 12: Power De-rating (Note F)

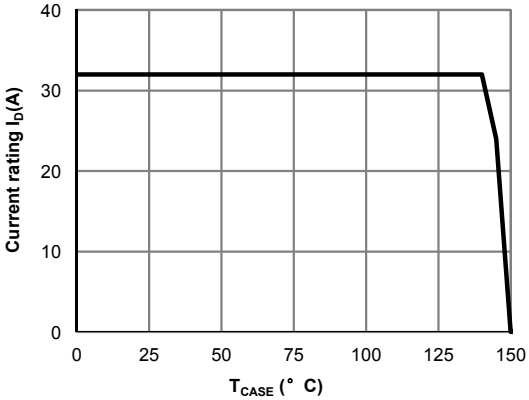


Figure 13: Current De-rating (Note F)

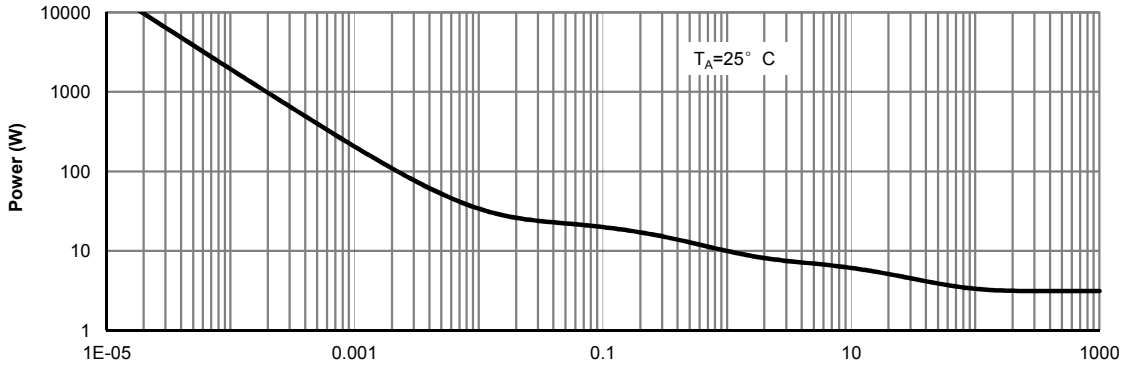


Figure 14: Single Pulse Power Rating Junction-to-Ambient (Note H)

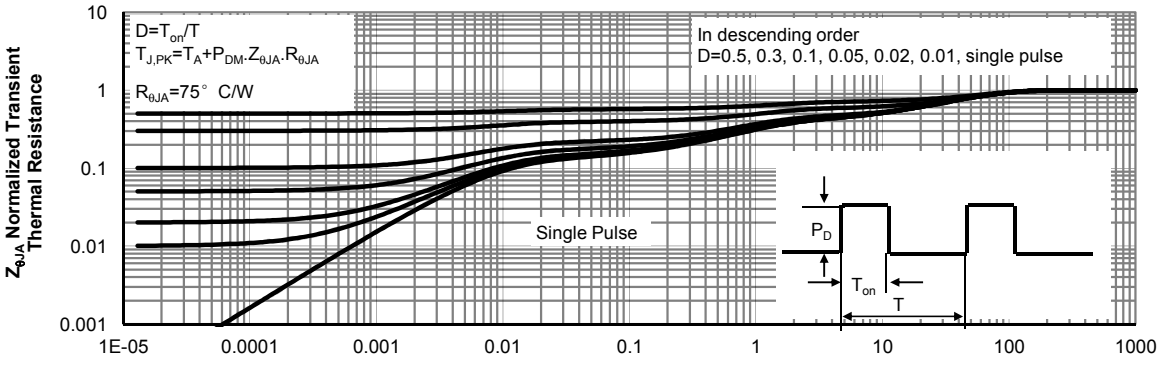
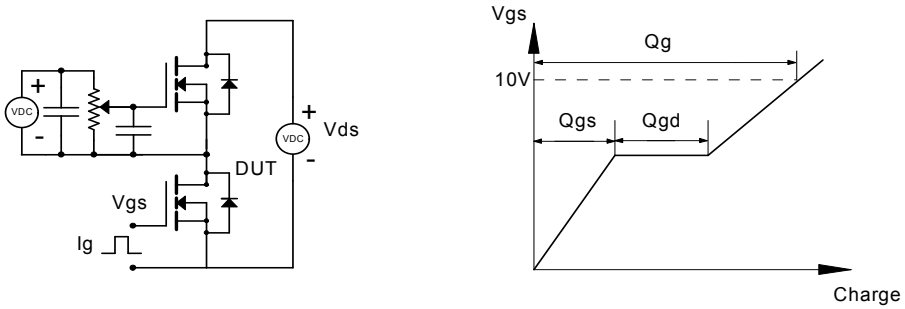
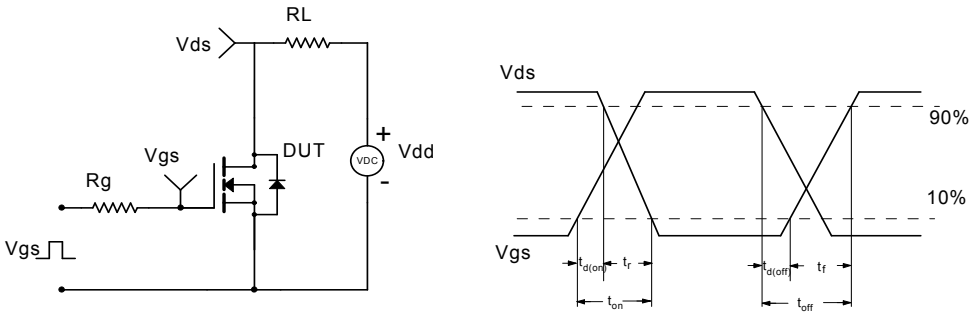


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)

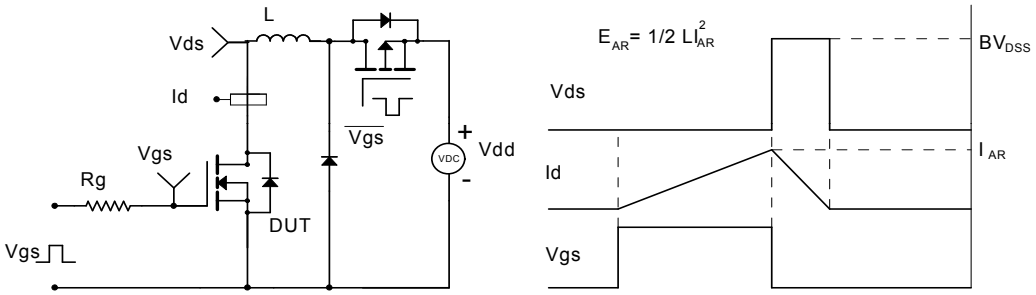
Gate Charge Test Circuit & Waveform



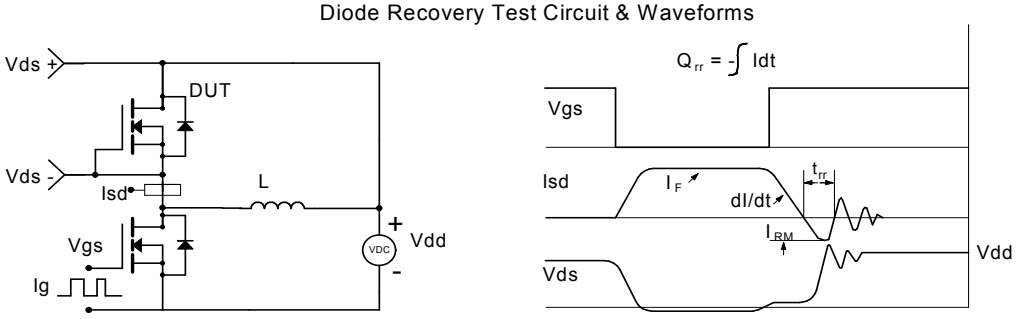
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



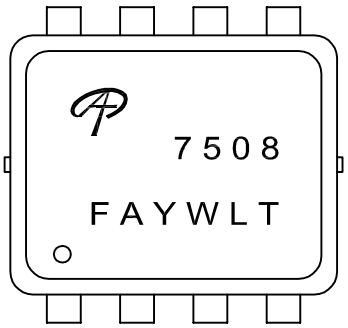
Diode Recovery Test Circuit & Waveforms



ALPHA & OMEGA SEMICONDUCTOR

Document No.	PD-01721
Version	A
Title	AON7508 Marking Description

DFN3X3 PACKAGE MARKING DESCRIPTION



Green product

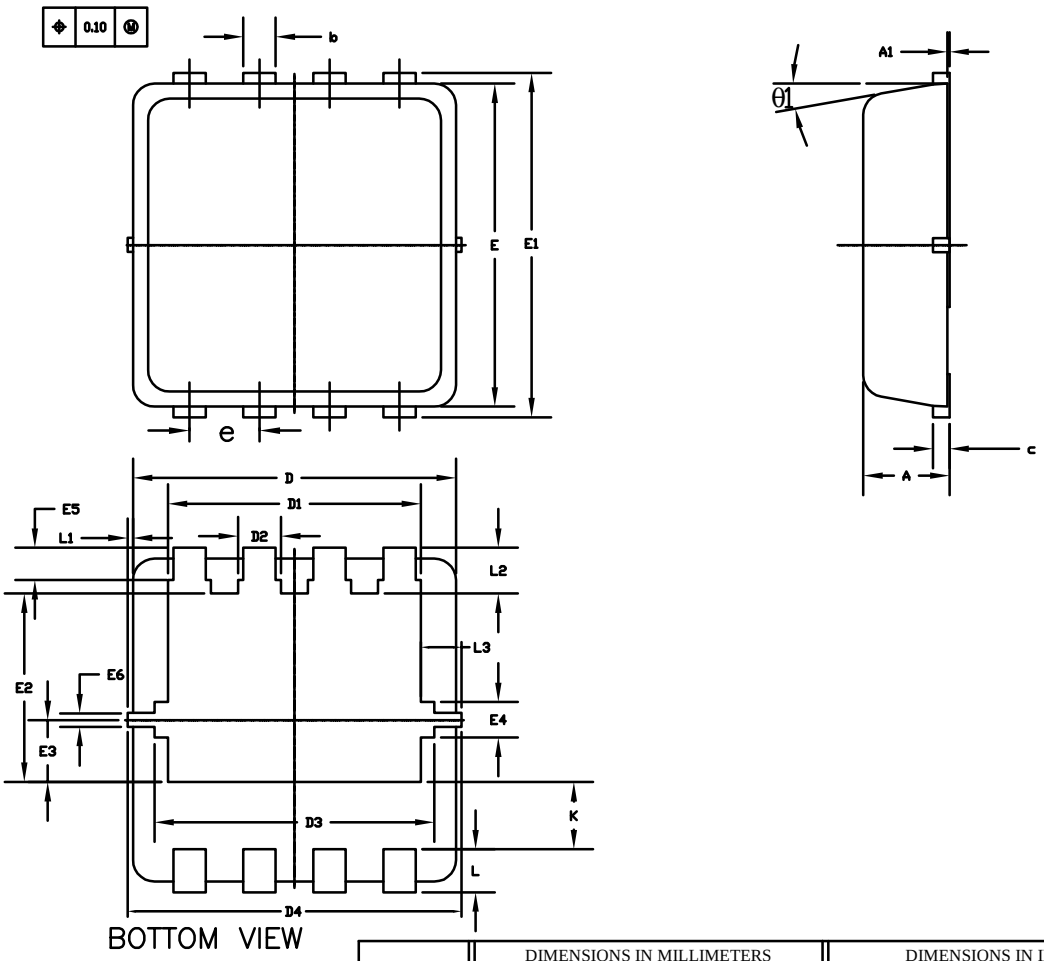
NOTE:
LOGO - AOS Logo
7508 - Part number code
F - Fab code
A - Assembly location code
Y - Year code
W - Week code
L&T - Assembly lot code

PART NO.	DESCRIPTION	CODE
AON7508	Green product	7508
AON7508L	Green product	7508

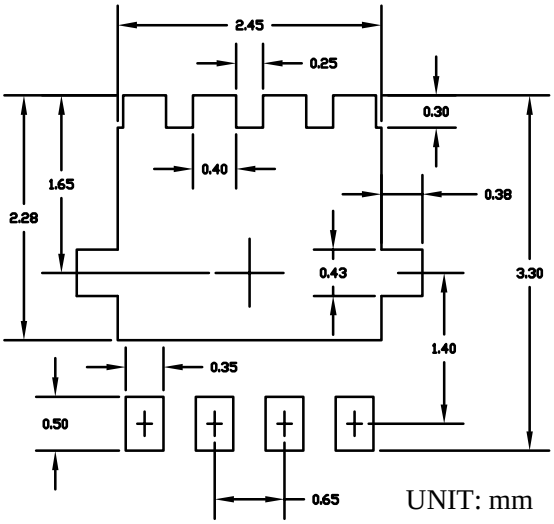
ALPHA & OMEGA SEMICONDUCTOR

Document No.	PO-00047
Version	G

DFN3x3A_8L_EP1_P PACKAGE OUTLINE



RECOMMENDED LAND PATTERN



UNIT: mm

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.70	0.80	0.90	0.028	0.031	0.035
A1	0.00	0.025	0.05	0.000	0.001	0.002
b	0.24	0.30	0.35	0.009	0.012	0.014
c	0.10	0.15	0.25	0.004	0.006	0.010
D	2.90	3.00	3.10	0.114	0.118	0.122
D1	2.25	2.35	2.45	0.089	0.093	0.097
D2	0.30	0.40	0.50	0.012	0.016	0.020
D3	2.50	2.60	2.70	0.098	0.102	0.106
D4	3.00	3.10	3.20	0.118	0.122	0.126
E	2.90	3.00	3.10	0.114	0.118	0.122
E1	3.10	3.20	3.30	0.122	0.126	0.130
E2	1.65	1.75	1.85	0.065	0.069	0.073
E3	0.48	0.58	0.68	0.019	0.023	0.027
E4	0.23	0.33	0.43	0.009	0.013	0.017
E5	0.20	0.30	0.40	0.008	0.012	0.016
E6	0.075	0.125	0.175	0.003	0.005	0.007
e	0.60	0.65	0.70	0.024	0.026	0.028
K	0.52	0.62	0.72	0.020	0.024	0.028
L	0.30	0.40	0.50	0.012	0.016	0.020
L1	0	0.05	0.10	0	0.002	0.004
L2	0.33	0.43	0.53	0.013	0.017	0.021
L3	0.275	0.375	0.475	0.011	0.015	0.019
θ1	0°	10°	12°	0°	10°	12°

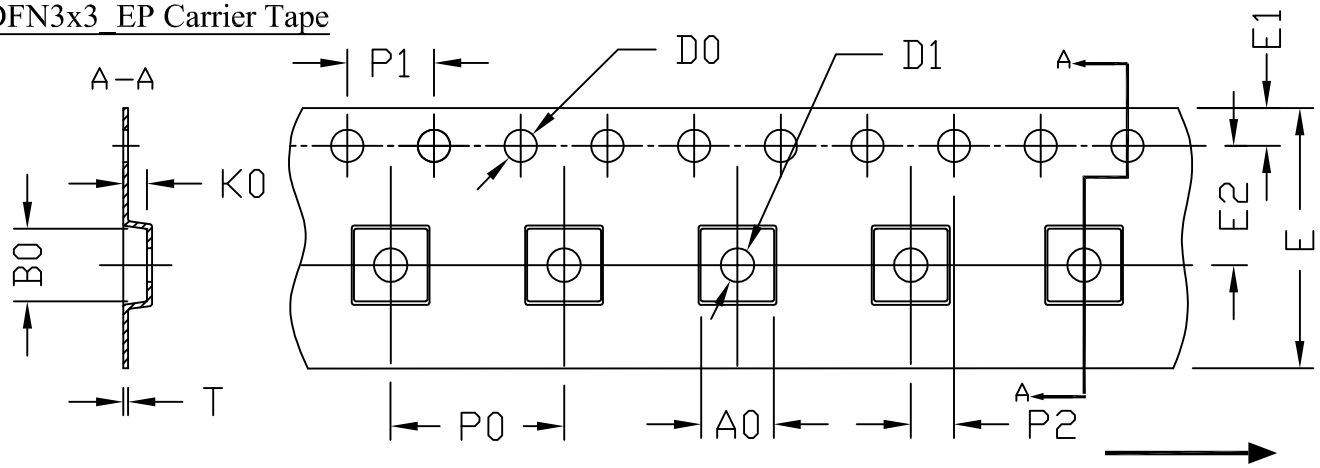
NOTE

1. PACKAGE DIMENSION IS EXCLUSIVE OF MOLD GATE BURR
2. PACKAGE DIMENSION IS EXCLUSIVE OF MOLD FLASH AND CUTTING BURR
3. CONTROLLING DIMENSION IS MILLIMETER.
   CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

ALPHA & OMEGA
SEMICONDUCTOR, LTD.

DFN3x3_EP Tape and Reel Data

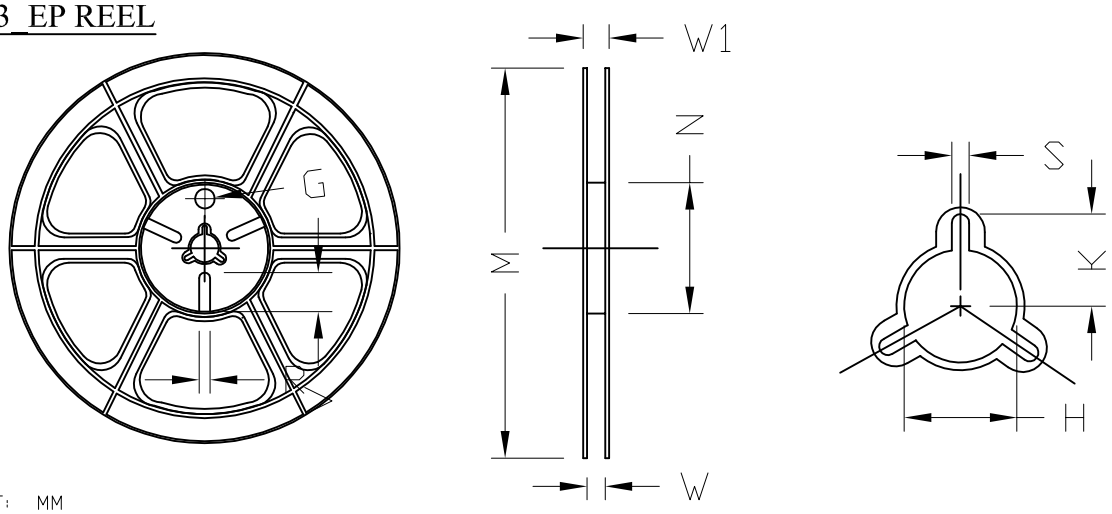
DFN3x3_EP Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
DFN3x3_EP	3.40 ±0.10	3.35 ±0.10	1.10 ±0.10	1.50 +0.10 −0	1.50 +0.10 −0	12.00 ±0.30	1.75 ±0.10	5.50 ±0.05	8.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.30 ±0.05

DFN3x3_EP REEL



UNIT: MM

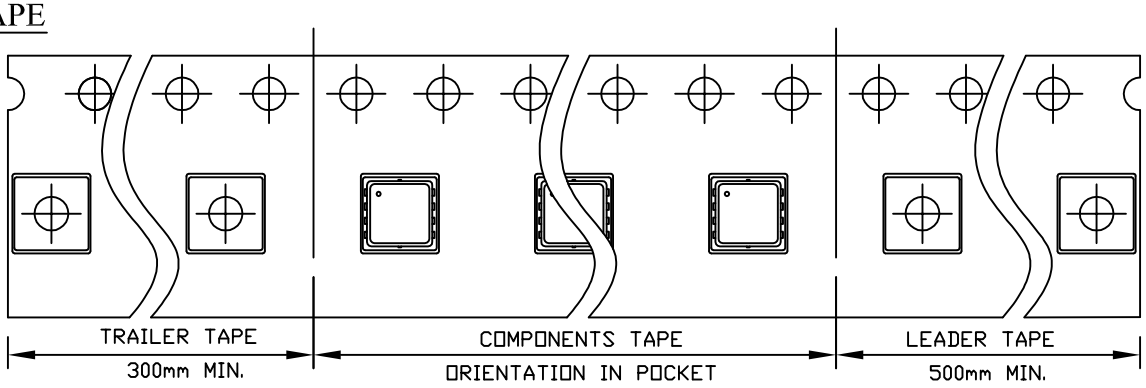
TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
12 mm	ø330	ø330.00 ±0.50	ø97.00 ±0.10	13.00 ±0.30	17.40 ±1.00	ø13.00 +0.50 −0.20	10.60	2.00 ±0.50	---	---	---

DFN3x3_EP TAPE

Leader / Trailer
& Orientation

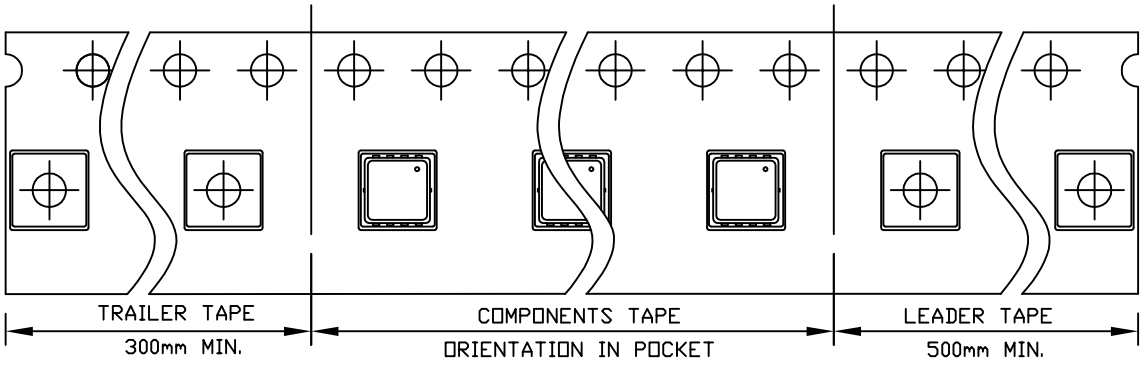
MOS

Unit Per Reel:
5000pcs



PIC

Unit Per Reel:
5000pcs



AOS Semiconductor
Product Reliability Report

AON7508, rev A

Plastic Encapsulated Device

ALPHA & OMEGA Semiconductor, Inc

www.aosmd.com

This AOS product reliability report summarizes the qualification result for AON7508. Accelerated environmental tests are performed on a specific sample size, and then followed by electrical test at end point. Review of final electrical test result confirms that AON7508 passes AOS quality and reliability requirements.

Table of Contents:

I. Product Description:

General Description:
• Latest Trench Power AlphaMOS (α MOS LV) technology
• Very Low RDS(on) at 4.5VGS
• Low Gate Charge
• High Current Capability
• RoHS and Halogen-Free Compliant

Application:
• DC/DC Converters in Computing, Servers, and POL
• Isolated DC/DC Converters in Telecom and Industrial

Detailed information refers to datasheet.

II. Die / Package Information:

	AON7508
Process	Standard sub-micron Low voltage N channel
Package Type	DFN 3x3A
Lead Frame	Cu
Die Attach	Ag epoxy
Bonding	Cu wire
Mold Material	Epoxy resin with silica filler
MSL (moisture sensitive level)	Level 1 based on J-STD-020

Note * based on information provided by assembler and mold compound supplier

ALPHA & OMEGA SEMICONDUCTOR

III. Result of Reliability Stress for AON7508

Test Item	Test Condition	Time Point	Lot Attribution	Total Sample size	Number of Failures	Standard
MSL Precondition	168hr 85℃ /85%RH +3 cycle reflow@260℃	-	11 lots	1815pcs	0	JESD22-A113
HTGB	Temp = 150 °c, Vgs=100% of Vgsmax	168hrs 500hrs 1000 hrs	1 lot 3 lots (Note A*)	308pcs 77pcs / lot	0	JESD22-A108
HTRB	Temp = 150 °c, Vds=80% of Vdsmax	168hrs 500hrs 1000 hrs	1 lot 3 lots (Note A*)	308pcs 77pcs / lot	0	JESD22-A108
HAST	130 +/- 2°c, 85%RH, 33.3 psi, Vgs = 100% of Vgs max	100 hrs	11 lots (Note A*)	605pcs 55pcs / lot	0	JESD22-A110
Pressure Pot	121°c, 29.7psi, RH=100%	96 hrs	11 lots (Note A*)	605pcs 55pcs / lot	0	JESD22-A102
Temperature Cycle	-65°c to 150°c, air to air	250 / 500 cycles	11 lots (Note A*)	605pcs 55pcs / lot	0	JESD22-A104

Note A: The reliability data presents total of available generic data up to the published date.

IV. Reliability Evaluation

FIT rate (per billion): 7
MTTF = 15704 years

The presentation of FIT rate for the individual product reliability is restricted by the actual burn-in sample size of the selected product (AON7508). Failure Rate Determination is based on JEDEC Standard JESD 85. FIT means one failure per billion hours.

Failure Rate = $Chi^2 \times 10^9$ **/ [**2 (N) (H) (Af)**]**
= 1.83×10^9 **/ [**2x (2x77x168+ 6x77x1000) x258**] =** 7
MTTF = 10^9 / FIT = 1.38×10^8hrs = 15704 years

Chi² = Chi Squared Distribution, determined by the number of failures and confidence interval
N = Total Number of units from HTRB and HTGB tests
H = Duration of HTRB/HTGB testing
Af = Acceleration Factor from Test to Use Conditions (Ea = 0.7eV and Tuse = 55℃)
Acceleration Factor [Af**]** = **Exp** [Ea / **k** (1/Tj u – 1/Tj s)]
Acceleration Factor ratio list:

	55 deg C	70 deg C	85 deg C	100 deg C	115 deg C	130 deg C	150 deg C
Af	258	87	32	13	5.64	2.59	1

Tj s = Stressed junction temperature in degree (Kelvin), K = C+273.16
Tj u = The use junction temperature in degree (Kelvin), K = C+273.16
K = Boltzmann's constant, 8.617164×10^{-5}eV / K